Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No. 98095DIV4	Serial No.: 10/008,653
	Applicant Gonzales	
	Filing Date November 9, 2001	Group 2815

U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Issue Date	Patentee	Class	Sub-Class	Filing Date
KPN		4,470,852	Sep. 11, 1984	Ellsworth			

FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

Examiner Initial		Document Number	Public. Date	County or Patent Office	Class	Sub-Class	Transl Y	Transl N

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KPN			Wolf et al. (Silicon Processing For The VLSI ERA, Volume 1: Process Technology, pp. 397-399, 1986)
Examiner [signature]			Date Considered 7/25/07

EXAMINER: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	Atty. Docket No. 98095DIV3	Serial No. 10/008,653
	Applicant Gonzalez et al.	
	Filing Date 11/9/01	Group

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